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# FDMA520PZ

#### June 2014

# Single P-Channel PowerTrench® MOSFET -20V, -7.3A, $30m\Omega$

#### **Features**

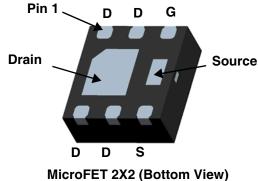
- Max  $r_{DS(on)} = 30m\Omega$  at  $V_{GS} = -4.5V$ ,  $I_D = -7.3A$
- Max  $r_{DS(on)} = 53m\Omega$  at  $V_{GS} = -2.5V$ ,  $I_D = -5.5A$
- Low profile 0.8mm maximum in the new package MicroFET 2X2 mm
- HBM ESD protection level > 3kV typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

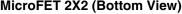


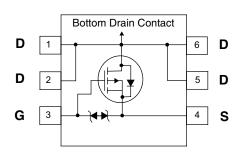
#### **General Description**

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.







#### MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage		-20	V	
$V_{GS}$	Gate to Source Voltage		±12	V	
	Drain Current -Continuous	(Note 1a)	-7.3	_	
l'D	-Pulsed		-24	A	
Б	Power Dissipation	(Note 1a)	2.4	10/	
P <sub>D</sub>	Power Dissipation	(Note 1b)	0.9	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

#### **Thermal Characteristics**

F	$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
F	$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
520	FDMA520PZ	MicroFET 2X2	7"	8mm	3000 units

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	octeristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to 25°C		-8.4		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$			-1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			±10	μΑ

#### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.6	-1.1	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = -250μA, referenced to 25°C		3.5		mV/°C
		$V_{GS} = -4.5V$ , $I_D = -7.3A$		26	30	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = -2.5V$ , $I_D = -5.5A$		42	53	mΩ
		$V_{GS} = -4.5V$ , $I_D = -7.3A$ , $T_J = 125$ °C		36	55	
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5V, I_{D} = -7.3A$		22		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 40V V - 0V	1235	1645	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = –10V, V <sub>GS</sub> = 0V, f = 1MHz	255	340	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	I - IIVII IZ	225	340	pF

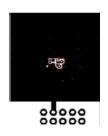
#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		10	20	ns
t <sub>r</sub>	Rise Time	$V_{DD} = -10V$ , $I_{D} = -7.3A$ $V_{GS} = -4.5V$ , $R_{GEN} = 6Ω$	29	47	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> 4.5V, R <sub>GEN</sub> - 012	83	133	ns
t <sub>f</sub>	Fall Time		74	119	ns
$Q_g$	Total Gate Charge	7.04	14	20	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DD} = -5V, I_{D} = -7.3A$ $V_{GS} = -4.5V$	2.9		nC
$Q_{gd}$	Gate to Drain "Miller" Charge	- VGS4.5V	4.4		nC

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current			-2	Α
$V_{SD}$	Source to Drain Diode Forward Voltage $V_{GS} = 0V$ , $I_S = -2A$		-0.8	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =–7.3A, di/dt = 100A/μs	30	45	ns
Q <sub>rr</sub>	Reverse Recovery Charge	1F7:5A, di/dt - 100A/μs	22	33	nC

1: R<sub>0,JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.



a. 52°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.145°C/W when mounted on a minimum pad of 2 oz copper

- 2: Pulse Test: Pulse Width < 300µs, Duty cycle < 2.0%.
  3: The diode connected between the gate and the source serves only as protection against ESD. No gate overvoltage rating is implied.

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

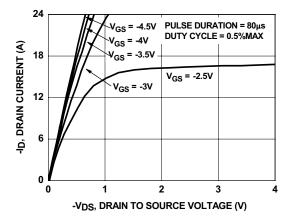


Figure 1. On-Region Characteristics

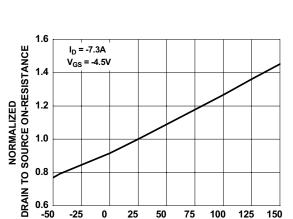


Figure 3. Normalized On-Resistance vs Junction Temperature

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

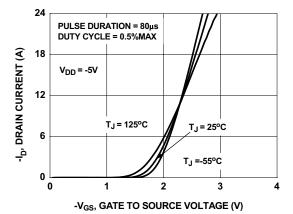


Figure 5. Transfer Characteristics

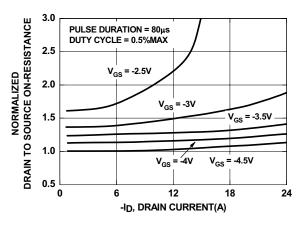


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

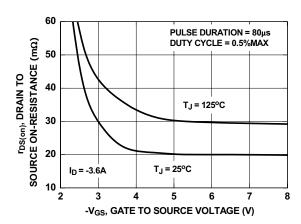


Figure 4. On-Resistance vs Gate to Source Voltage

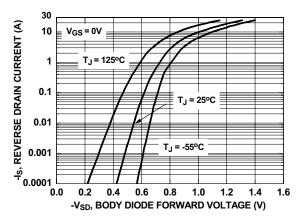


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

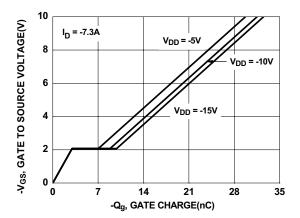


Figure 7. Gate Charge Characteristics

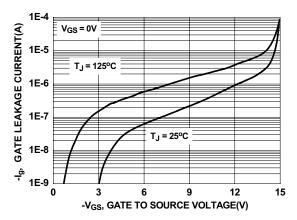


Figure 9. Gate Leakage Current vs Gate to Source Voltage

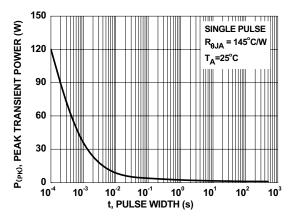


Figure 11. Single Pulse Maximum Power Dissipation

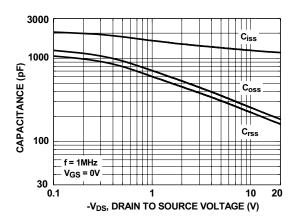


Figure 8. Capacitance vs Drain to Source Voltage

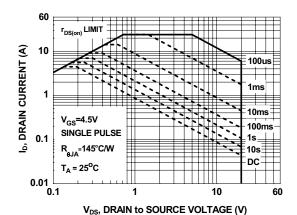


Figure 10. Forward Bias Safe Operating Area

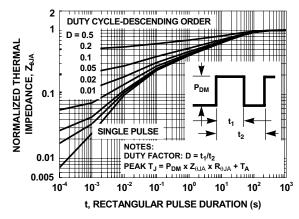
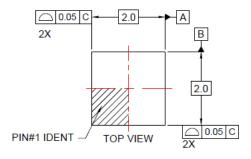
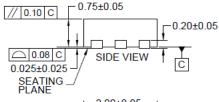
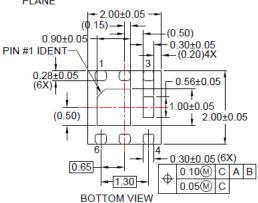


Figure 12. Transient Thermal Response Curve

### **Dimensional Outline and Pad Layout**

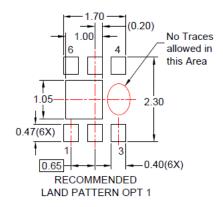


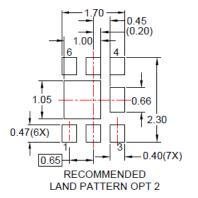




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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP06Lrev4.







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